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# Copper CVD: Applications and Potential Recycle

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# PRESENTATION OUTLINE

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- ▲ Applications for copper CVD.
- ▲ Introduction to precursor chemistry.
- ▲ Chemical delivery, processing issues.
- ▲ Abatement versus recycle of CVD effluent.
- ▲ Summary.

# Applications for copper CVD

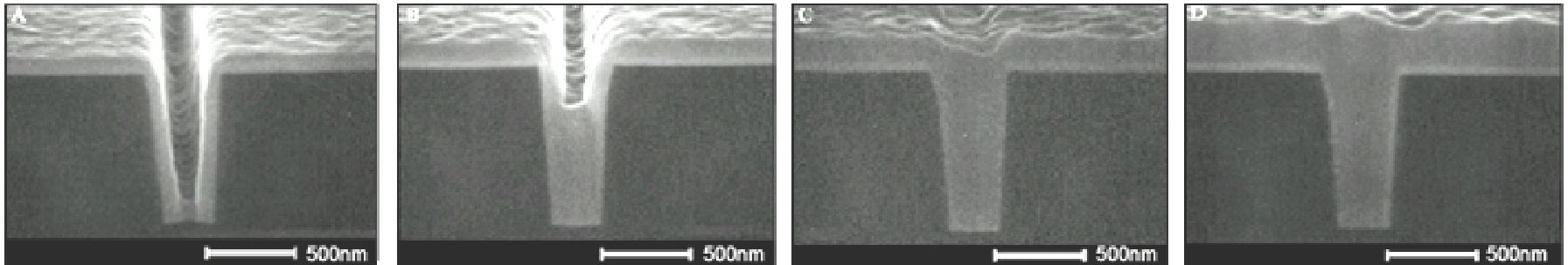
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- ▲ Provide ultra-thin conformal copper seed layers for electroplated copper.
- ▲ Enable new copper CVD Superfill.
- ▲ All 'dry' CVD copper full-fill capability vs. electroplated copper
  - Avoids the use of stand alone e-plating tool.
  - All metal film processing from diffusion barrier to copper seed to full-fill achieved on one tool without vacuum break.

# Copper CVD superfill using CupraSelect

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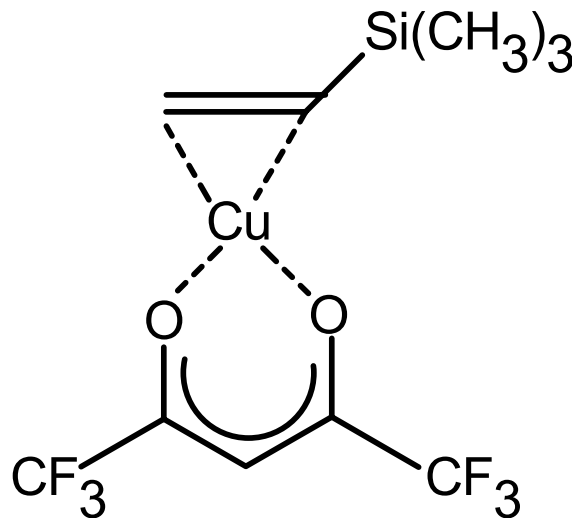
- ▲ Use of catalytic iodine surfactant. E.S. Hwang, J. Lee, Chem. Mater. 2000, 12, 2076- 2081.
- ▲ Copper fills from the bottom of the feature first.



# CUPRA SELECT®

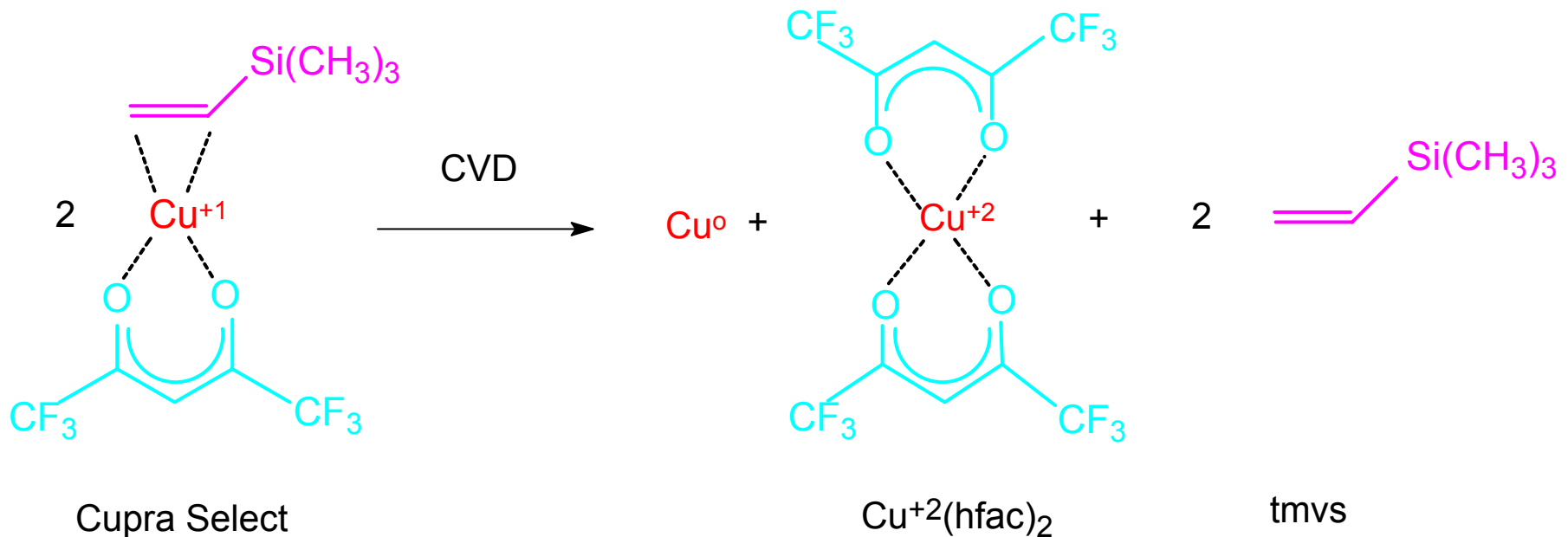
- ▲ Stable yellow liquid  $\text{Cu}(\text{hfac})(\text{tmvs})$ , premier copper precursor.
- ▲ Vapor pressure 1 Torr @ 60°C.
- ▲ Provides 99.99% copper , 1.85  $\mu\text{ohm cm}^1$ , 5000 A/min.
- ▲ Conformality > 90%

<sup>1</sup>J. Norman et al Thin Solid Films 262 (1995) 46-51



# CVD COPPER FILM GROWTH

## ▲ Metallization by disproportionation



# METALLIZATION CHEMISTRY

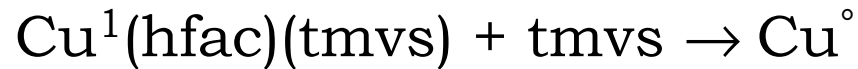
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- ▲ Selective deposition onto conductors due to key electron transfer step.
- ▲ Superior metallization process by the use of additives.
  - tmvs for stable precursor delivery.
  - hfac and water (separately or as HDH) for enhanced metallization.
  - water addition alone promotes adhesion.

# EVOLUTION OF CUPRA SELECT PROCESSING WITH ADDITIVES

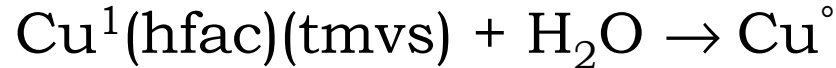
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- ▲ Enhanced thermal stability during DLI evaporation.



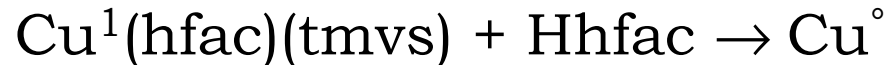
T. Omstead (Sandia)

- ▲ Enhanced deposition rate for copper.



A. V. Gelatos et al Appl Phys Lett., 63 (20) (1993) 2842.

- ▲ Enhanced deposition rate, uniformity and reflectivity.

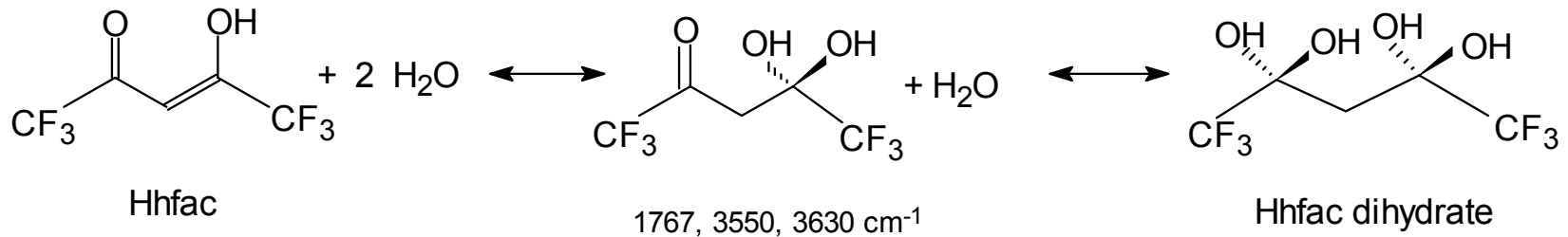


J. Norman et al Conference proceedings ULSI-IX 1994 MRS



## COMBINING THE ACCELERANT ADDITIVES Hhfac AND WATER INTO ONE COMPOUND: Hhfac DIHYDRATE

- ▲ Release of Hhfac and H<sub>2</sub>O occur under CVD conditions, assuming adequate residence times for dissociation in the CVD chamber.
- ▲ Cu(hfac)(tmvs)/hydrate blend can be stabilized by tmvs addition.
- ▲ Improved adhesion of copper to some TiN, but additional water needed for Ta and TaN.



# SUMMARY OF ADDITIVE TRENDS

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	Adhesion	Uniformity	Dep. Rate	Resistance	Reflectivity	DLI Performance
<b>tmvs</b>	0	0	(-) <sup>1</sup>	(-) <sup>2</sup>	(-) <sup>3</sup>	+
<b>Hhfac</b>	0	+	+	0	+	(-)
<b>H<sub>2</sub>O</b>	+	(+)	+	(-) <sup>4</sup>		(-)
<b>HDH</b>	(+) <sup>5</sup>	+	+	0	+	(-)

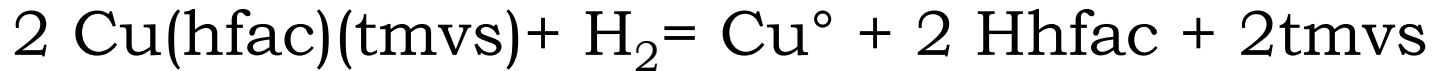
## Legend:

- + = improves
- = degrades
- 0 = no effect
- () = lesser effect

- 1) Disproportionation suppressed.
- 2) Resistance can appear higher due to film roughness.
- 3) Degraded by higher roughness.
- 4) Excess water yield copper oxides.
- 5) Improves adhesion on some TiN.

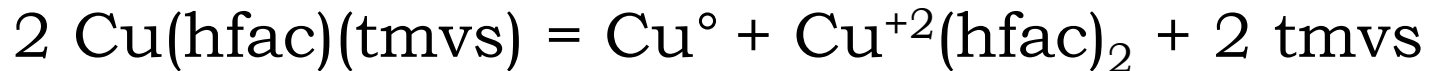
# Hydrogen as a reducing agent:

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Arita et al J. Electrochem. Soc., Vol 142, No9, 3173 (1995)

▲ Compare to disproportionation:



# WAFER METALLIZATION SCENARIO

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- ▲ At 2000A/min, 0.25m 6:1 AR
- ▲ On an 8 inch wafer 0.5 microns copper film corresponds to 0.144g copper metal.
- ▲ Assume 30% utilization efficiency of copper precursor entering the reactor.
- ▲ 2.5g of CupraSelect will be consumed during the process step, but approx 70% of this remains unchanged as it exits the process chamber as effluent.

# ABATEMENT SCENARIOS FOR REACTOR EFFLUENT

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- ▲ Destructive capture of CVD effluent.
  - pyrolysis in a hot-box.
  - chemical absorption by a caustic scrubber.
  - ultimate disposal of copper waste.
- ▲ Reversible physical entrapment for recycle
  - no copper waste for disposal, environmentally benign.
  - complete recycle for copper containing CVD byproducts.
  - lowered COO to end user.

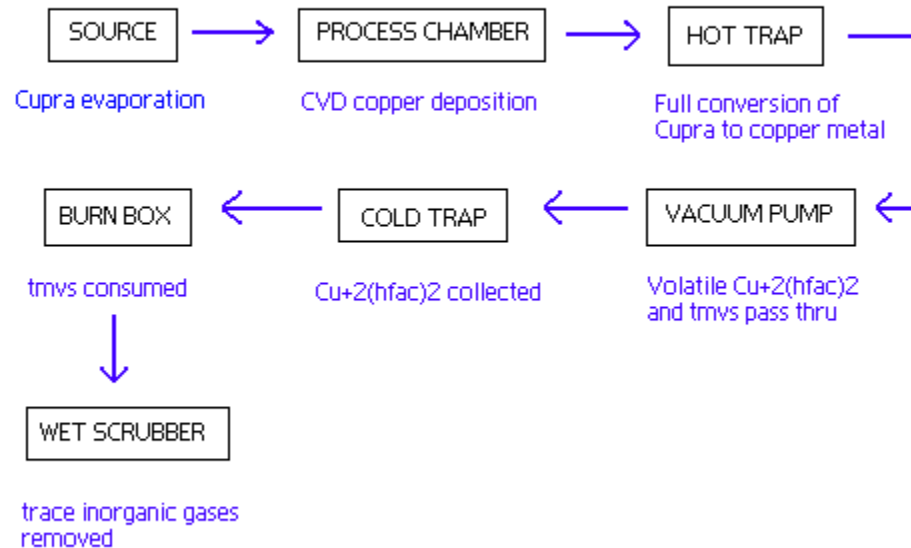
# Destructive abatement

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- ▲ Precursor vapor contacted with alkaline metal oxides at high temperature to fragment fluorocarbon ligands to give metal fluorides, HF, CHF<sub>x</sub> etc.
- ▲ Any residual flammable vapors are combusted in burn box to give carbon dioxide, water and HF
- ▲ HF vapors and carbon dioxide need alkaline scrubber for absorption
- ▲ Copper deposited as waste metal or metal fluoride for disposal.
- ▲ High value-added molecules irreversibly consumed.

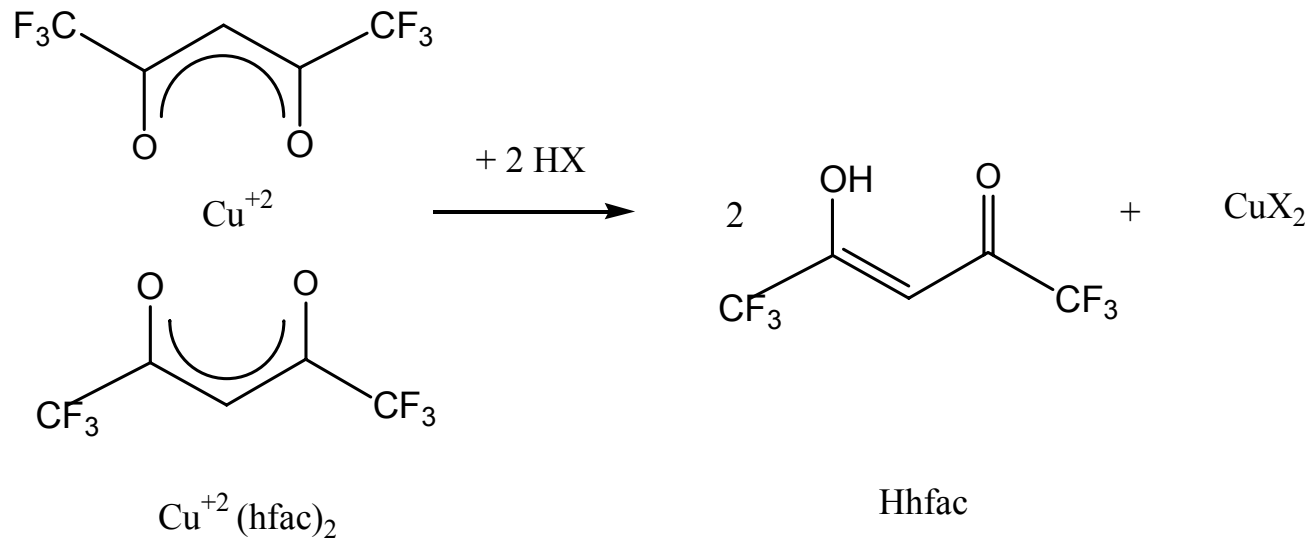
# Collection of copper metal and $\text{Cu}^{+2}(\text{hfac})_2$

## ▲ Applied Materials US 6099649



# Regeneration of Hhfac ligand

## ▲ Air Products US 6046364



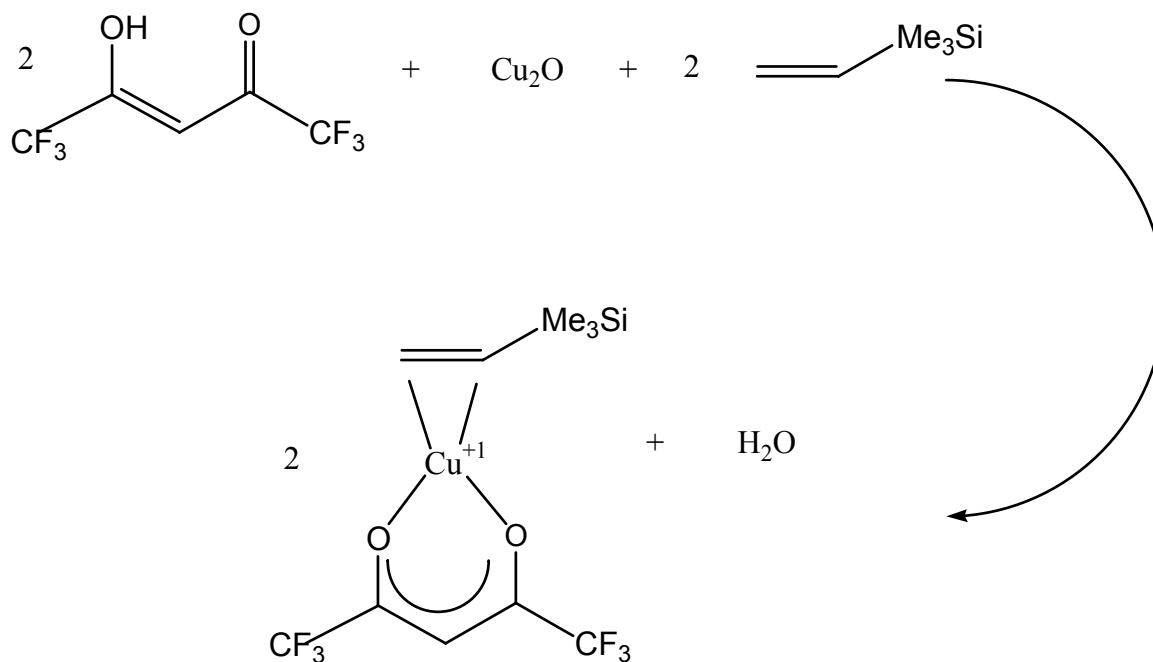
V.P. 1 Torr @ 77C

Bpt. 70C



# Production of CupraSelect

- ▲ Regenerated Hhfac recycled back to give fresh precursor. Air Products US 6096913.



# SUMMARY

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- ▲ CupraSelect is attractive for commercial implementation of copper CVD for e-plate seed, CVD superfill, all 'dry' full-fill CVD .
  - Adaptable precursor properties
  - Simple thermal CVD process.
  - Excellent film properties.
  - Potential for minimal environmental impact via fluorinated ligand and copper recycle.